



DMTH8008LPSQ

80V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	Rds(on) max	I _D Tc = +25°С
	7.8mΩ @ V _{GS} = 10V	91A
80V	11mΩ @ V _{GS} = 4.5V	77A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC-DC Converters
- Load Switch

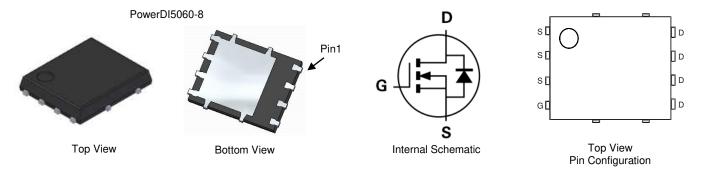
Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On-State Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH8008LPSQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/guality/product-definitions/

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)



Ordering Information (Note 4)

	Part Number	Case	Packaging		
	DMTH8008LPSQ-13	PowerDI5060-8	2,500/Tape & Reel		
Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.					

 See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



)|| = Manufacturer's Marking TH8008LSQ = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 19 = 2019) WW = Week (01 to 53)

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Maximum Ratings (@Tc = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			VDSS	80	V
Gate-Source Voltage			Vgss	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 7)	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	ID	91 64	A
Maximum Continuous Body Diode Forward Current (Note 7)			Is	69	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			Ідм	360	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	360	A
Avalanche Current, L = 0.1mH (Note 8)			las	23	A
Avalanche Energy, L = 0.1mH (Note 8)			Eas	26.5	mJ

Thermal Characteristics (@T_C = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	1.6	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	93	°C/W
Total Power Dissipation (Note 6)	TA = +25°C	PD	3.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	44	°C/W
Total Power Dissipation (Note 7)	Tc = +25°C	PD	100	W
Thermal Resistance, Junction to Case (Note 7)		Rejc	1.5	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Electrical Characteristics (@T_C = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)	Symbol	WIIII	ιyρ	Max	onit	Test condition	
Drain-Source Breakdown Voltage	BV _{DSS}	80	_	_	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS		_	1	μA	$V_{DS} = 64V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	VGS(TH)	1.3	_	2.8	V	$V_{DS} = V_{GS}, I_D = 1mA$	
Statia Drain Course On Desistance			5	7.8	<u> </u>	VGS = 10V, ID = 14A	
Static Drain-Source On-Resistance	R _{DS(ON)}		8	11	mΩ	VGS = 4.5V, ID = 12A	
Diode Forward Voltage	Vsd	—	0.8	1.2	V	VGS = 0V, IS = 14A	
DYNAMIC CHARACTERISTICS (Note 10)	•					·	
Input Capacitance	Ciss	—	2345	_		V _{DS} = 40V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	_	842	—	pF		
Reverse Transfer Capacitance	Crss	—	51.9	_			
Gate Resistance	Rg	_	1.7	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_G	_	21.7	—			
Total Gate Charge (V _{GS} = 10V)	QG	_	41.2	—	nC	$V_{DD} = 40V, I_D = 2A$	
Gate-Source Charge	Qgs	_	5.0	—	no		
Gate-Drain Charge	Q _{GD}	_	10.6	—			
Turn-On Delay Time	td(on)	_	5.8	—		$V_{DD} = 40V, V_{GS} = 10V,$ $I_D = 2A, R_G = 1.6\Omega$	
Turn-On Rise Time	t _R	_	5.4	—			
Turn-Off Delay Time	tD(OFF)	_	24.5	—	ns		
Turn-Off Fall Time	tF	_	43.2	—			
Body Diode Reverse Recovery Time	trr	_	61	—	ns	1= 0.4 di/dt 100.4/up	
Body Diode Reverse Recovery Charge	Qrr	_	181	—	nC	- I _F = 2A, di/dt = 100A/μs	

Notes:

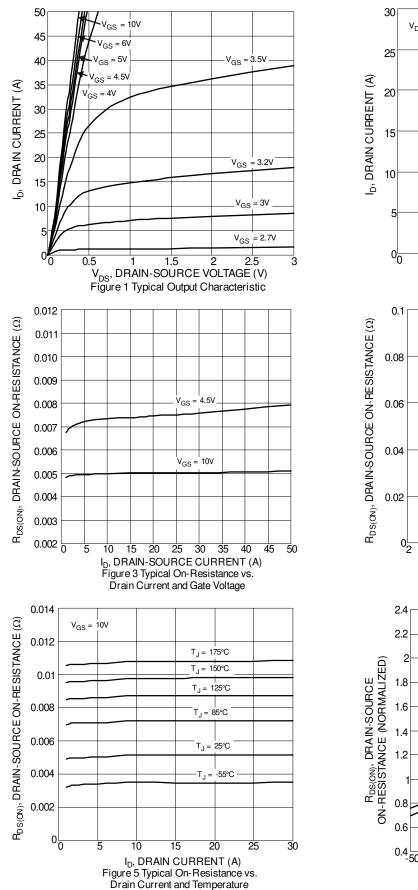
Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
Thermal resistance from junction to soldering point (on the exposed drain pad).

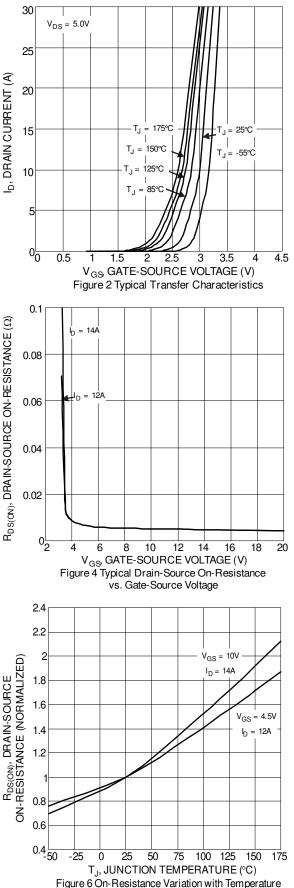
8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.

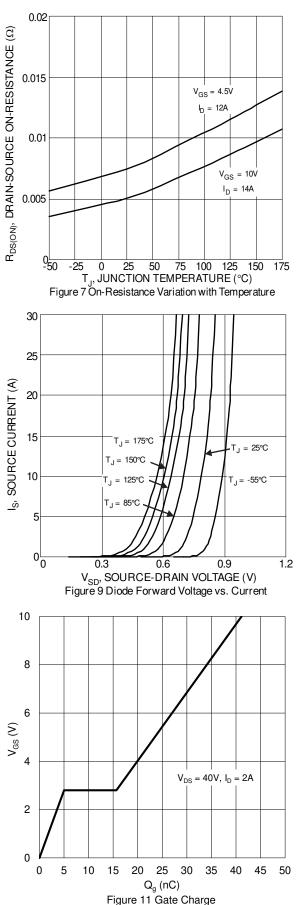




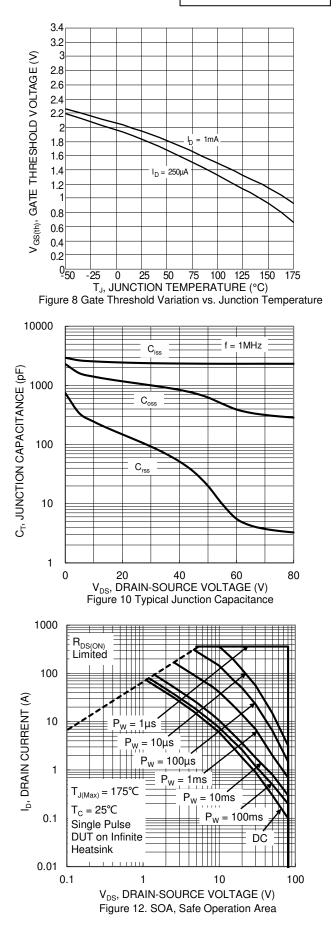






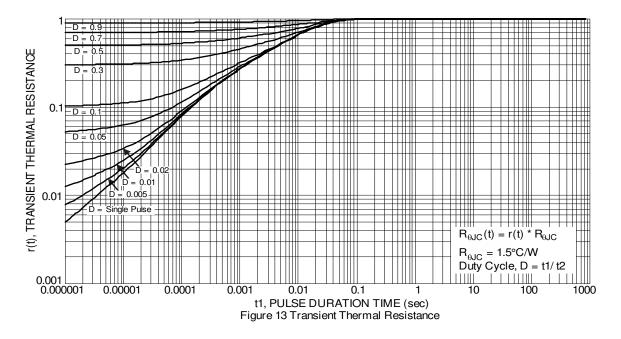


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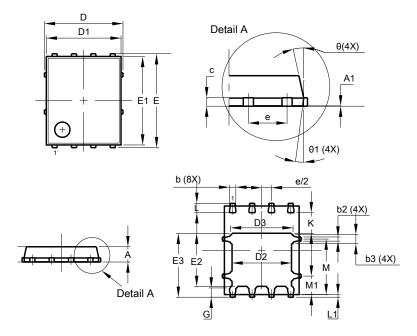




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

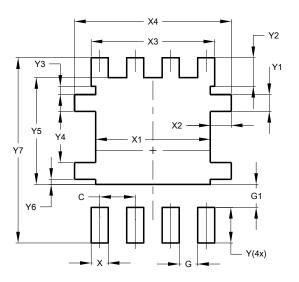


PowerDI5060-8						
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
A1	0.00	0.05	-			
b	0.33	0.51	0.41			
b2	0.200	0.350	0.273			
b3	0.40	0.80	0.60			
С	0.230	0.330	0.277			
D	ļ	5.15 BSC	;			
D1	4.70	5.10	4.90			
D2	3.70	4.10 3.90				
D3	3.90 4.30 4.10					
E	6.15 BSC					
E1	5.60	6.00	5.80			
E2	3.28	3.68	3.48			
E3	3.99	4.39 4.19				
е	1.27 BSC					
G	0.51	0.71	0.61			
K	0.51	-	-			
L	0.51	0.71	0.61			
L1	0.100	0.200	0.175			
М	3.235	4.035	3.635			
M1	1.00	1.40	1.21			
Θ	10°	12°	11°			
Θ1	6°	8°	7°			
Al	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610



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